HI-REL DATA SHEET

HM 65688

16 k x 4
ULTIMATE CMOS SRAM

4

FEATURES

- ACCESS TIME : 35*/45/55 ns
- VERY LOW POWER CONSUMPTION
  ACTIVE : 175.0 mW (typ)
  STANDBY : 2.0 µW (typ)
  DATA RETENTION : 0.8 µW (typ)
- WIDE TEMPERATURE RANGE : - 55 TO + 125°C
- 300 MILS WIDTH PACKAGE
- TTL COMPATIBLE INPUTS AND OUTPUTS
- ASYNCHRONOUS
- SINGLE 5 VOLT SUPPLY
- EQUAL CYCLE AND ACCESS TIME
- GATED INPUTS : NO PULL-UP/DOWN RESISTORS ARE REQUIRED

* Preliminary

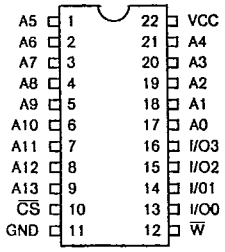
DESCRIPTION

The HM 65688 is a very low power CMOS static RAM organized as 16384 x 4 bits. It is manufactured using the MHS high performance CMOS technology named super SCMOS.
With this process, MHS is the first to bring the solution for applications where fast computing is as mandatory as low consumption, such as the aerospace electronics, the portable instruments or embarked systems.
Utilizing an array of six transistors (6T) memory cells, the HM 65688 combines an extremely low standby supply current (Typical value = 0.1 µA) with a fast access time at 35 ns over the full temperature range.
The high stability of the 6T cell provides excellent protection against soft errors due to noise.
Extra protection against heavy ions is given by the use of an epitaxial layer of a P substrate.
The HM 65688 is 100 % processed following the test methods of MIL STD 883C and/or ESA/SCC 9000, making it ideally suitable for military/space applications that demand superior levels of performance and reliability.

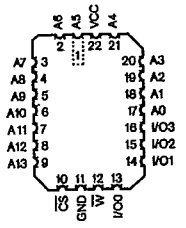
PACKAGES

Ceramic 300 mils, 22 pins, DIL. LCC, 22 pins.

Pinout DIL 22 pins (top view)

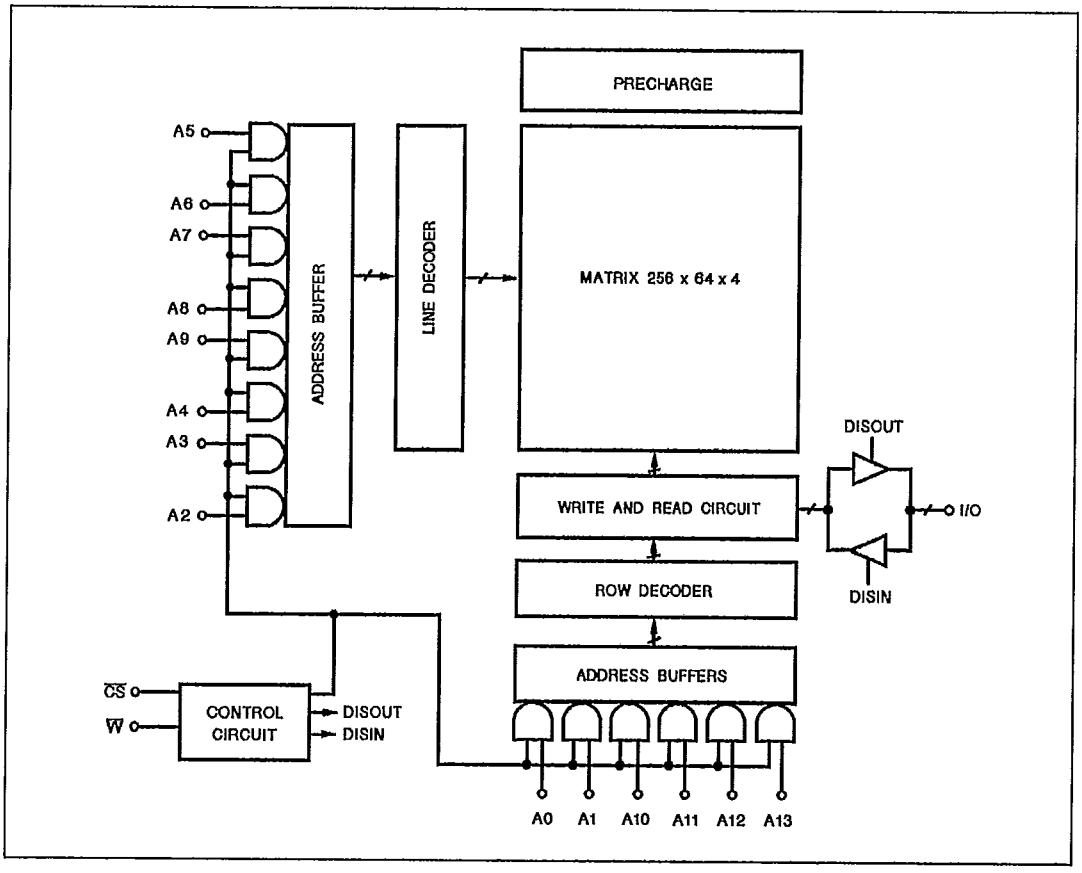


Pinout LCC 22 pins (top view)

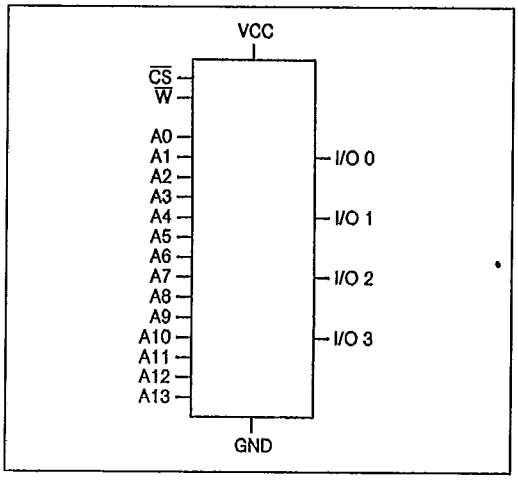


* preliminary

BLOCK DIAGRAM



LOGIC SYMBOL



PIN NAMES

A0-A13 : Address inputs	GND : Ground
I/O0-I/O3 : Inputs/Outputs	$\overline{CS}$: Chip-Select
Vcc : Power	$\overline{W}$: Write Enable

TRUTH TABLE

$\overline{CS}$	$\overline{W}$	INPUTS/OUTPUTS	MODE
H	X	Z	Deselect/Power down
L	H	Data out	Read
L	L	Data in	Write

L = low, H = high, X = H or L, Z = high impedance.

ABSOLUTE MAXIMUM RATINGS

Supply voltage to GND potential : - 0.5 V to + 7.0 V
Input or Output voltage applied : (Gnd - 0.3 V) to (Vcc + 0.3 V)
Storage temperature : - 65°C to + 150°C
Electro static discharge voltage > 2000 V (MIL STD 883, METHOD 3015)

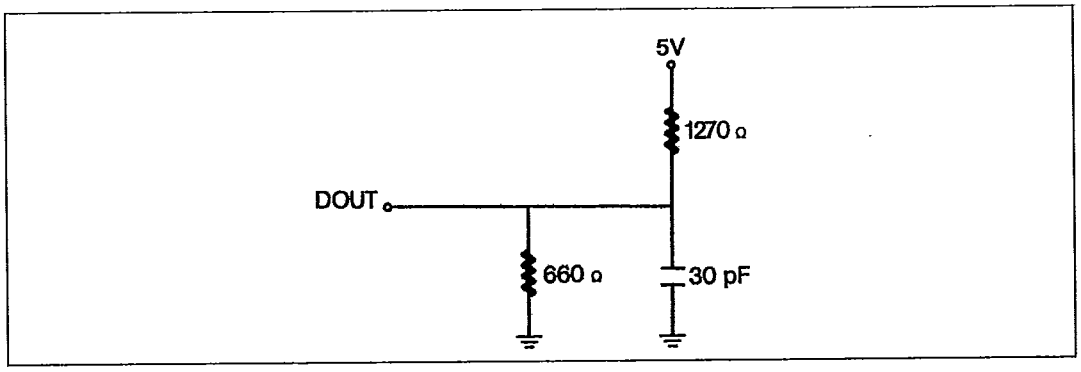
OPERATING RANGE	OPERATING VOLTAGE	OPERATING TEMPERATURE
Military	Vcc = 5 V ± 10 %	- 55°C to + 125°C
Industrial	Vcc = 5 V ± 10 %	- 40°C to + 85°C

ELECTRICAL CHARACTERISTICS
DC PARAMETERS : MIL STD 883C FOR GROUP A (Subgroups 1, 2, 3, 4)

Parameter	Description	65688 Q	65688 B	65688 S	65688	65688 C	Unit	Value	Note 8
ICCSB (1)	Standby supply current	20	15	20	15	20	mA	Max	M
ICCSB1 (2)	Standby supply current (I/M)	500	5/50	100/500	5/50	100/500	µA	Max	M
ICCOP (3)	Operating supply current	100	75	100	75	100	mA	Max	M
ICC (4)	Operating supply current	20	15	20	15	20	mA	Max	M
II/O (5)	Input/Output leakage current	± 1	± 1	± 1	± 1	± 1	µA	Max	M
VIL (6)	Input low voltage	0.8	0.8	0.8	0.8	0.8	V	Max	T
VIH (6)	Input high voltage	2.2	2.2	2.2	2.2	2.2	V	Min	T
VOL (7)	Output low voltage	0.4	0.4	0.4	0.4	0.4	V	Max	M
VOH (7)	Output high voltage	2.4	2.4	2.4	2.4	2.4	V	Min	M
C IN	Input capacitance	5	5	5	5	5	pF	Max	G
C OUT	Output capacitance	7	7	7	7	7	pF	Max	G

Notes :
1. $\overline{CS1}$ > = VIH, CS2 < VIL
2. $\overline{CS1}$ > = Vcc - 0.3V, CS2 < = 0.3V, Output current = 0 mA, I = Industrial M = Military
3. Vcc max, Iout = 0 mA, Duty cycle 100 %, F = max, Vin = Vcc / Gnd
4. $\overline{CS1}$ < = VIL, CS2 > ≅ VIH, Iout = 0 mA, Vin = Gnd to Vcc
5. Vcc = 5.5V, Vin = Gnd to Vcc
6. VIH max = Vcc + 0.3V, VIL min = - 0.3V or - 1V pulse width 50 ns.
7. Vcc min, IOL = 4 mA, IOH = - 1 mA
8. Including open/short test or inputs clamp voltage.
   G - Guaranted - Not tested : Parameter measured at design validation and at any design change.
   M - Measured : Parameter measured and data-log capability.
   T - Tested : Parameter verification during testing.

OUTPUT LOAD

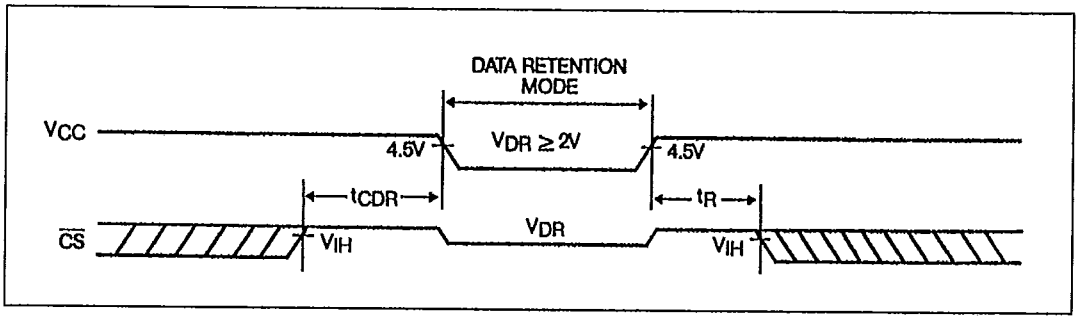


DATA RETENTION MODE

MHS CMOS RAM's are designed with battery backup in mind. Data retention voltage and supply current are guaranteed over temperature. The following rules insure data retention :

1. Chip select ($\overline{CS}$) must be held high during data retention ; within Vcc to Vcc + 0.3 V.
2. $\overline{CS}$ must be kept between Vcc + 0.3 V and 70 % of Vcc during the power up and power down transitions.
3. The RAM can begin operation > 45 ns after Vcc reaches the minimum operating voltage (4.5V).

TIMING



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DATA RETENTION CHARACTERISTICS

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL (9)	MAXIMUM	UNIT	NOTE 8
VCCDR	Vcc for data retention	2.0	—	—	V	T
TCDR	Chip deselect to data retention time	0.0	—	—	ns	
TR	Operation recovery time	TAVAV (10)	—	—	ns	
ICCDR1 (10)	Data retention current @ 2.0 V : HM-65688 (B)-	—	0.1	3/20.0	µA	M
	HM-65688 S/C/Q	—	0.1	30/200.0	µA	M
ICCDR2 (11)	Data retention current @ 3.0 V : HM-65688 (B)-	—	0.3	3/30.0	µA	G
	HM-65688 S/C/Q	—	0.3	30/300.0	µA	G

Notes : 9. TA = 25°C.
10. TAVAV = Read cycle time.
11. $\overline{CS}$ = Vcc, Vin = Gnd/Vcc, this parameter is only tested to Vcc = 2 V.
12. I = Industrial / M = Military.

ELECTRICAL CHARACTERISTICS
AC PARAMETERS : MIL STD 883C FOR GROUP A (SUBGROUPS 7, 8, 9, 10, 11)

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AC CONDITIONS :

Input pulse levels : Gnd to 3.0 V
Input rise : 5 ns
VCC : 5 V ± 10 %

Input timing reference levels : 1.5 V
Output load : 1 TTL gate + 30 pF

WRITE CYCLE : Industrial and Military Specification

SYMBOL	PARAMETER *	65688 Q	65688 B	65688 S	65688	65688 C	UNIT	VALUE
TAVAV	Write cycle time	35	45	45	55	55	ns	min
TAVWL	Address set-up time –	0	0	0	0	0	ns	min
TAVWH	Address valid to end of write	35	45	45	55	55	ns	min
TDVWH	Data set-up time	22	25	25	25	25	ns	min
TELWH	$\overline{CS}$ low to write end	35	45	45	55	55	ns	min
TWLQZ (12)	Write low to high Z	15	15	15	20	20	ns	max
TWLWH	Write pulse width	30	40	40	50	50	ns	min
TWHAX	Address hold to end of write	5	5	5	5	5	ns	min
TWHDX	Data hold time	3	3	3	3	3	ns	min
TWHQX (12)	Write high to low Z	0	0	0	0	0	ns	min

Note : 12. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

* : All parameters only tested and screened during full speed functional test.
For subgroups 7 and 8, functional test is performed at 1 MHz with VIL = OV and VIH = 3V.

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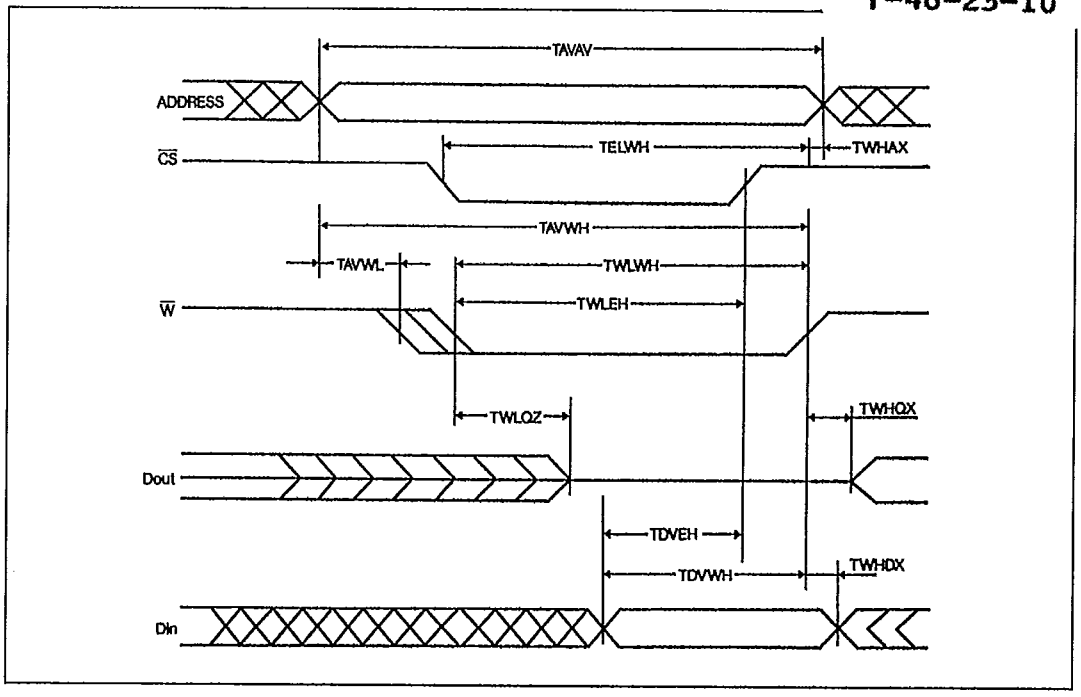
WRITE CYCLE

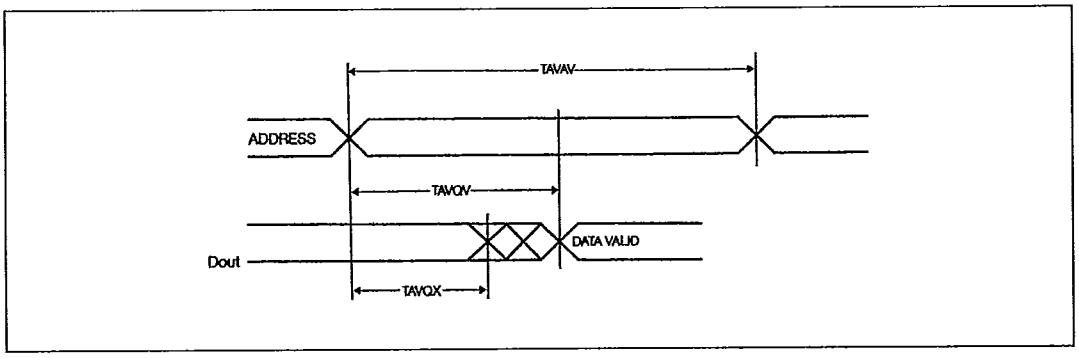


Note : 13. The internal write time of the memory is defined by the overlap of $\overline{CS}$ LOW and $\overline{W}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.

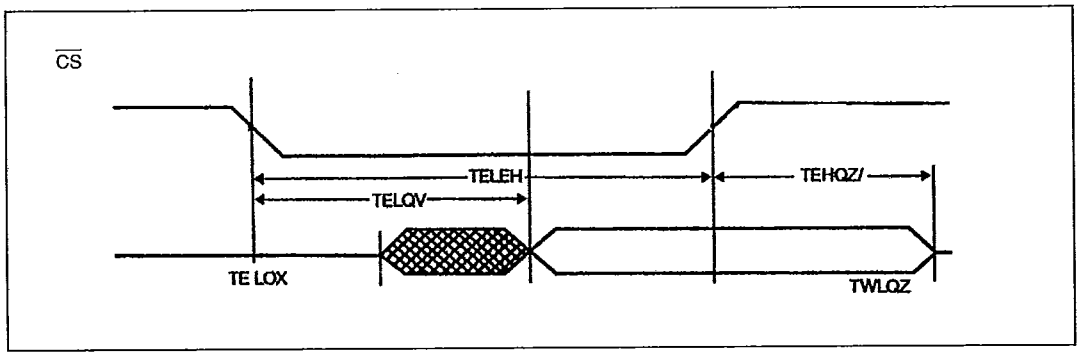
READ CYCLE : Industrial and Military specification

SYMBOL	PARAMETER *	65688 Q	65688 B	65688 S	65688	65688 C	UNIT	VALUE
TAVAV	Read cycle time	35	45	45	55	55	ns	min
TAVQV	Address access time	35	45	45	55	55	ns	max
TAVQX	Address valid to low Z	3	3	3	3	3	ns	min
TELQV	Chip-select access time	35	45	45	55	55	ns	max
TELQX	$\overline{CS}$ low to low Z	5	5	5	5	5	ns	min
TEHQZ	$\overline{CS}$ high to high Z	35	45	45	55	55	ns	max

READ CYCLE nb 1 (notes 13, 14)



READ CYCLE nb 2 (notes 13, 15)



Notes : 13. $\overline{W}$ is high for read cycle.
14. Device is continuously selected, $\overline{CS}$ = VIL.
15. Address valid prior to or coincident with $\overline{CS}$ transitive low.

ORDERING INFORMATION

T-46-23-10

PROCESS FLOW

Package	Device Type	Grade	Type	Level/Class	Lot Acceptance Level
HM1	65688	S	S	B	2 *

- Device Type 65688: 16K x 4 low power Static RAM
- Type S: - 9 : Industrial; - 2 : Military; - 8 : Military Program; M : MIL STD 883C; S : SCC 9000; C : CECC 90000; D : Dice HI-REL
- Lot Acceptance Level 2 *: 1 : LAT 1; 2 : LAT 2; 3 : LAT 3

Package:
- 1 - Ceramic DIL 22
- 4 - LCC 22 pins
- 0 - Chip form
- W - Wafer form

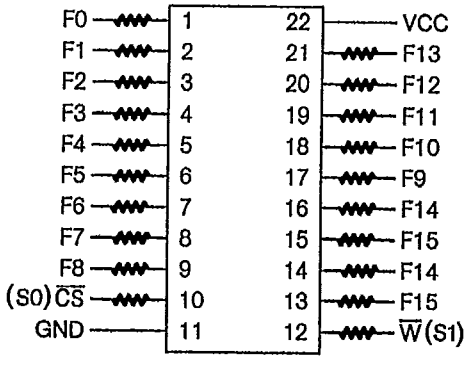
Grade:
- B : High speed/Low current
- S : High speed/Medium current
- Blank : Medium speed/Lowcurrent
- C : Medium speed/Medium current
- Q : Very high speed/Medium current

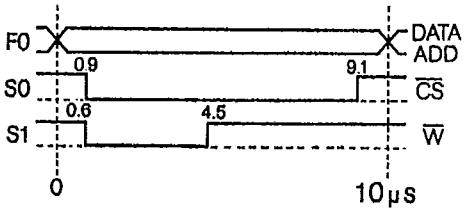
Level/Class:
- Blank : MHS test method
- B Class : MIL STD 883C
- B Level : SCC 9000
- C Level : SCC 9000
- B Level : CECC 90000

* only SCC 9000 specification

	PACKAGED PRODUCT						DIE FORM	
SUFFIX →	- 2	- 8	MB	CB	SB	SC	- 2	DB
DESCRIPTION →	- 55°C TO + 125°C	MILITARY PROGRAM	MIL-STD 883C CLASS B	COMPLIANT WITH CECC 90000 LEVEL B	COMPLIANT WITH SCC 9000 LEVEL B	COMPLIANT WITH SCC 9000 LEVEL C	25 °C AND 125 °C PROBE	HI-REL FLOW

BURN IN SCHEMATICS





VCC = 5 V (– 0, + 0,5)
R = 1KΩ per pin

F0 = 91.6 KHz ± 20 %
Fn = 1/2 F n-1

S0 & S1 : programmable signals for write / read cycles

MATRA M H S

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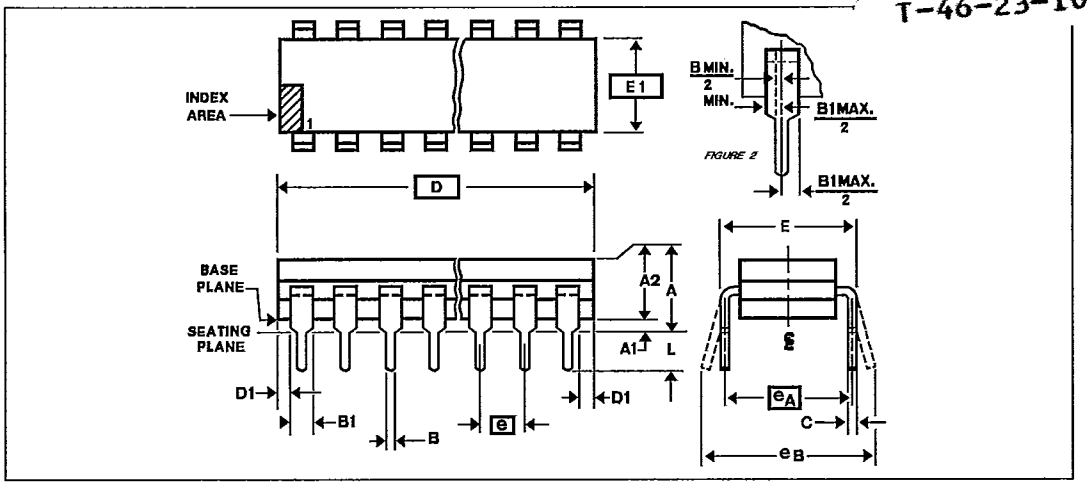
PACKAGE OUTLINES



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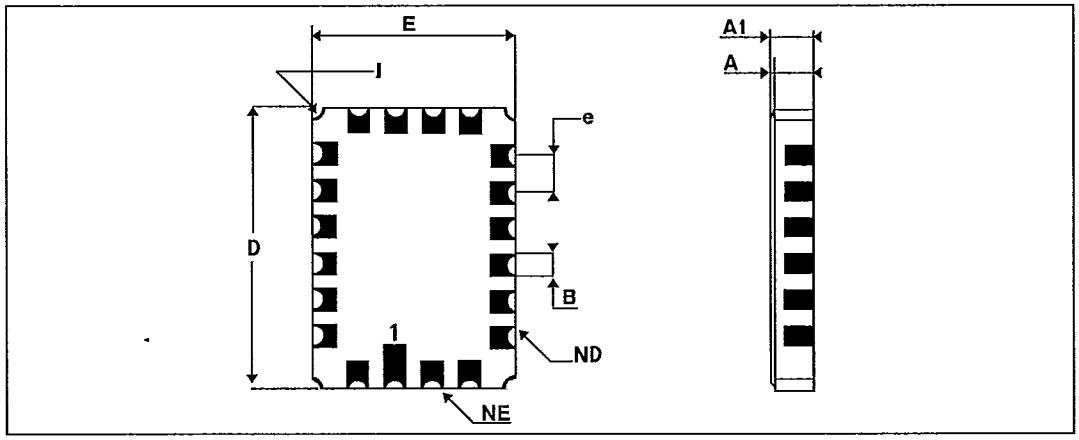
22 PINS CERDIP .300

		A	A1	A2	B	B1	C	D	D1	E	E1	e	eA	eB	L
MM	MIN	–	0.51	3.17	0.36	0.89	0.20	26.92	0.13	7.82	7.24	2.54	7.62	–	3.05
	MAX	5.84	–	4.95	0.58	1.78	0.38	28.19	–	8.00	7.87	BSC	BSC	10.82	5.08
INCHES	MIN	–	.020	.125	.014	.035	.008	1.060	.005	.308	.285	.100	.300	–	.125
	MAX	.230	–	.195	.023	.070	.015	1.110	–	.315	.310	BSC	BSC	.426	.200



22 LDS .050 CENTER LEADLESS RECTANGULAR CHIP CARRIER

		A	A1	B	D	E	e	h	j	ND	NE
MM	MIN	1.37	1.62	0.15	12.31	7.24	1.27		0.30	7	4
	MAX	1.67	1.93	–	12.57	7.49	BSC		RAD		
INCHES	MIN	.054	.064	.006	.485	.285	.050		.012	7	4
	MAX	.066	.076	–	.495	.295	BSC		RAD		